

Physics of Semiconductor Devices

p-n junction (depletion width)

Problem

A silicon p-n diode has a doping of $N_D = 8 \times 10^{15} \frac{1}{cm^3}$ and $N_A = 2 \times 10^{16} \frac{1}{cm^3}$. What are the depletion width in the n-region, the depletion width in the p-region, and the built-in potential at 300K? Use the depletion approximation.

For Si: $n_i = 1.5 \times 10^{10} \frac{1}{cm^3}$, $\epsilon_r = 11.9$.

Attention: The parameters are changing everytime. These results are calculated with the above mentioned values.

Useful physical constants:

$$\begin{aligned} \text{Boltzmann constant: } & k_B = 1.38 \times 10^{-23} \frac{J}{K} \\ \text{Elementary charge: } & e = 1.602 \times 10^{-19} As \\ \text{Vacuum permittivity: } & \epsilon_0 = 8.854 \times 10^{-12} \frac{As}{Vm} \end{aligned}$$

Useful formulas:

Permittivity:

$$\epsilon = \epsilon_0 * \epsilon_r \quad (1)$$

Built-in voltage, contact potential:

$$V_{bi} = \frac{k_B * T}{e} * \ln\left(\frac{N_D * N_A}{n_i^2}\right) \quad (2)$$

Depletion width (no external bias):

$$W = \sqrt{\frac{2 * \epsilon * (N_D + N_A) * V_{bi}}{e * N_D * N_A}} \quad (3)$$

Depletion width in the p-region:

$$W_p = \frac{N_D * W}{N_D + N_A} \quad (4)$$

Depletion width in the n-region:

$$W_n = \frac{N_A * W}{N_A + N_D} \quad (5)$$

Solution:

Note: To get the correct SI-units:

$$N_D = 8 * 10^{15} \frac{1}{cm^3} = 8.10^{21} \frac{1}{m^3}$$

$$N_A = 2 * 10^{16} \frac{1}{cm^3} = 2 * 10^{22} \frac{1}{m^3}$$

Built-in voltage, contact potential:

$$V_{bi} = \frac{k_B * T}{e} * \ln\left(\frac{N_D * N_A}{n_i^2}\right) = \frac{1.38 * 10^{-23} * 300}{1.602 * 10^{-19}} * \ln\left(\frac{8.10^{21} * 2 * 10^{22}}{(1.5 * 10^{10})^2}\right) = \underline{0.7052V} \quad (6)$$

Depletion width (no external bias):

$$W = \sqrt{\frac{2 * \epsilon * (N_D + N_A) * V_{bi}}{e * N_D * N_A}} = \sqrt{\frac{2 * 11.9 * 8.854 * 10^{-12} * (8.10^{21} + 2 * 10^{22}) * 0.7052}{1.602 * 10^{-19} * 8.10^{21} * 2 * 10^{22}}} = 4.029 * 10^{-7} m \quad (7)$$

Depletion width in the p-region:

$$W_p = \frac{N_D * W}{N_D + N_A} = \frac{8.10^{21} * 4.029 * 10^{-7}}{8.10^{21} + 2 * 10^{22}} = \underline{1.151 * 10^{-7} m} \quad (8)$$

Depletion width in the n-region:

$$W_n = \frac{N_A * W}{N_A + N_D} = \frac{2 * 10^{22} * 4.029 * 10^{-7}}{2 * 10^{22} + 8.10^{21}} = \underline{2.8779 * 10^{-7} m} \quad (9)$$

Control:

$$1. N_A > N_D \implies W_n > W_p$$

$$2. W = W_n + W_p = 2.8779 * 10^{-7} + 1.151 * 10^{-7} = 4.0289 * 10^{-7} m$$